

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	(memory near1 cell near1 storage) near10 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:41
2	BRS	L2	622	(memory near1 cell) near10 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:35
3	BRS	L3	0	(memory near1 cell) near10 (voltage and current) near10 (resistance)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:37
4	BRS	L4	0	(memory) near10 (voltage and current) near10 (resistance)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:38
5	BRS	L5	0	(memory) near10 (voltage and current) near10 (resist\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	2306	(memory) near10 (voltage or current) near10 (resist\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:40
7	BRS	L7	243	(memory near1 cell near1 storage) near10 (voltage or current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:43
8	BRS	L8	2	(memory near1 cell near1 storage) near10 (voltage or current) near5 (resistance)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/19 14:44

	U	1	Document ID	Title	Current OR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 5726083 A	Process of fabricating dynamic random access memory device having storage capacitor low in contact resistance and small in leakage current through tantalum oxide film	438/210
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 61177699 A	DYNAMIC TYPE SEMICONDUCTOR MEMORY DEVICE	